

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







HiPerFRED²

 $V_{RRM} = 200 V$ $I_{FAV} = 2x \quad 30 A$ $t_{rr} = 35 \text{ ns}$

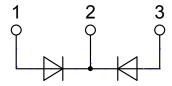
High Performance Fast Recovery Diode Low Loss and Soft Recovery Common Cathode

Part number

DPG60C200QB



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-3P

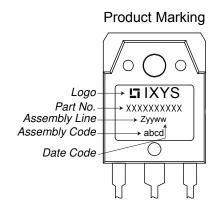
- Industry standard outline compatible with TO-247
- RoHS compliant
- Epoxy meets UL 94V-0



Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockii	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			200	V
I _R	reverse current, drain current	V _R = 200 V	$T_{VJ} = 25^{\circ}C$			1	μΑ
		$V_R = 200 V$	$T_{VJ} = 150^{\circ}C$			0.1	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			1.34	V
		$I_F = 60 \text{ A}$				1.63	V
		I _F = 30 A	T _{VJ} = 150°C			1.06	V
		$I_F = 60 \text{ A}$				1.39	V
I _{FAV}	average forward current	T _C = 140°C	T _{VJ} = 175°C			30	Α
		rectangular d = 0.5					1 1 1 1
V _{F0}	threshold voltage		T _{VJ} = 175°C			0.70	V
r _F	slope resistance	ss calculation only				10.5	mΩ
R _{thJC}	thermal resistance junction to case)				0.95	K/W
R _{thCH}	thermal resistance case to heatsin	k			0.25		K/W
P _{tot}	total power dissipation		$T_{c} = 25^{\circ}C$			160	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			360	Α
CJ	junction capacitance	V _R = 150 V f= 1 MHz	$T_{VJ} = 25^{\circ}C$		42		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25^{\circ}C$		3		Α
		$I_F = 30 \text{ A}; V_R = 130 \text{ V}$	$T_{VJ} = 125$ °C		7		Α
t _{rr}	reverse recovery time	} -di₅/dt = 200 A/μs	$T_{VJ} = 25^{\circ}C$		35		ns
		ı	$T_{VJ} = 125$ °C		55		ns



Package TO-3P				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal 1)			50	Α	
T _{VJ}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				5		g	
M _D	mounting torque		0.8		1.2	Nm	
F _c	mounting force with clip		20		120	N	



Part number

D = Diode

P = HiPerFRED

G = extreme fast

60 = Current Rating [A]

C = Common Cathode

200 = Reverse Voltage [V] QB = TO-3P (3)

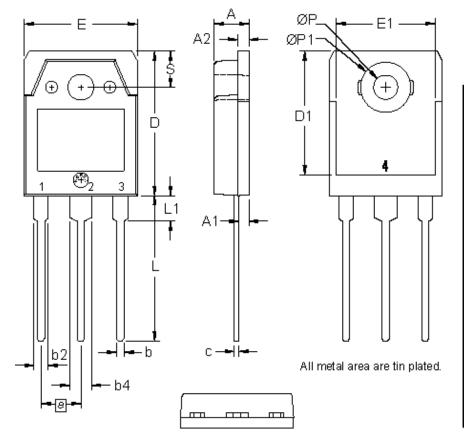
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG60C200QB	DPG60C200QB	Tube	30	502213

Similar Part	Package	Voltage class
DPG60C200HB	TO-247AD (3)	200
DPF60C200HB	TO-247AD (3)	200
DPF60C200HJ	ISOPLUS247 (3)	200

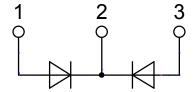
Equivalent Circuits for Simulation			* on die level	T _{VJ} = 175 °C
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	0.7		V
R _{0 max}	slope resistance *	7.9		$m\Omega$



Outlines TO-3P



Dim.	Millir	neter	Inc	Inches	
DIIII.	min	max	min	max	
Α	4.70	4.90	0.185	0.193	
A1	1.30	1.50	0.051	0.059	
A2	1.45	1.65	0.057	0.065	
b	0.90	1.15	0.035	0.045	
b2	1.90	2.20	0.075	0.087	
b4	2.90	3.20	0.114	0.126	
С	0.55	0.80	0.022	0.031	
D	19.80	20.10	0.780	0.791	
D1	16.90	17.20	0.665	0.677	
Е	15.50	15.80	0.610	0.622	
E1	13.50	13.70	0.531	0.539	
е	5.45	5.45 BSC		BSC	
Г	19.80	20.20	0.780	0.795	
L1	3.40	3.60	0.134	0.142	
ØР	3.20	3.40	0.126	0.134	
ØP1	6.90	7.10	0.272	0.280	
S	4.90	5.10	0.193	0.201	





Fast Diode

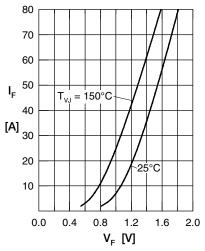


Fig. 1 Forward current I_F versus V_F

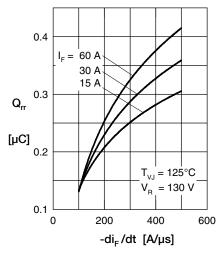


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

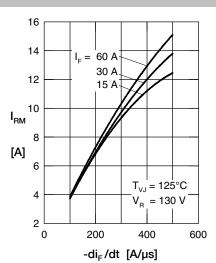


Fig. 3 Typ. reverse recov. current $I_{\rm RM}$ versus $-{\rm di_F}/{\rm dt}$

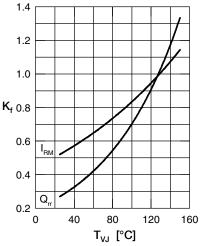


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

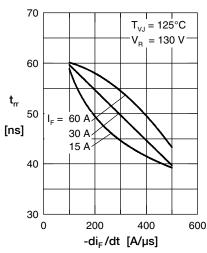
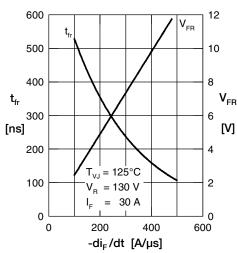


Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_{E}/dt$



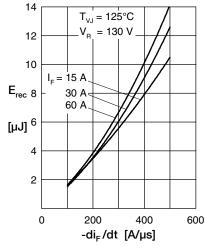


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

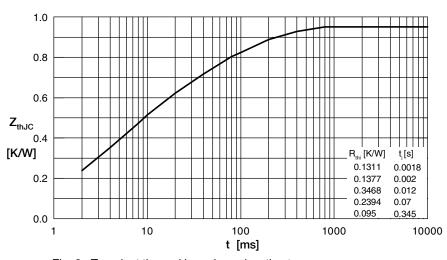


Fig. 8 Transient thermal impedance junction to case